

MOSFET

500V CoolMOS™ CE Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and indoor lighting.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

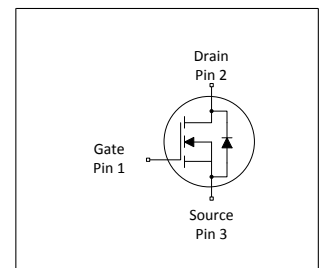


Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|----------------------|-------|----------|
| $V_{DS} @ T_{j,max}$ | 550 | V |
| $R_{DS(on),max}$ | 0.19 | Ω |
| I_D | 24.8 | A |
| $Q_{g,typ}$ | 47.2 | nC |
| $I_{D,pulse}$ | 63 | A |
| $E_{oss@400V}$ | 4.42 | μ J |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|-------------------|---------|----------------|
| IPA50R190CE | PG-TO 220 FullPAK | 5R190CE | see Appendix A |

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------------------------------|----------------|------------|------|--------------|------------------|-----------------------------------------------------------------------------------------------------------|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 24.8 15.7 | A | $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 63 | A | $T_C=25^\circ\text{C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 339 | mJ | $I_D=7.7\text{A}$; $V_{DD} = 50\text{V}$ |
| Avalanche energy, repetitive | E_{AR} | - | - | 0.51 | mJ | $I_D=7.7\text{A}$; $V_{DD} = 50\text{V}$ |
| Avalanche current, repetitive | I_{AR} | - | - | 7.7 | A | - |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 50 | V/ns | $V_{DS} = 0\dots 400\text{V}$ |
| Gate source voltage | V_{GS} | -20 -30 | - | 20 30 | V | static; AC ($f > 1\text{ Hz}$) |
| Power dissipation (Full PAK) | P_{tot} | - | - | 32 | W | $T_C=25^\circ\text{C}$ |
| Operating and storage temperature | T_j, T_{stg} | -40 | - | 150 | $^\circ\text{C}$ | - |
| Mounting torque | - | - | - | 50 | Ncm | M2.5 screws |
| Continuous diode forward current | I_S | - | - | 8.1 | A | $T_C=25^\circ\text{C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 63.0 | A | $T_C = 25^\circ\text{C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | - | - | 15 | V/ns | $V_{DS} = 0\dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$ |
| Maximum diode commutation speed ³⁾ | di/dt | - | - | 500 | A/ μs | $V_{DS} = 0\dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$ |
| Insulation withstand voltage for TO-220FP | V_{ISO} | - | - | 2500 | V | V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$ |

2 Thermal characteristics

Table 3 Thermal characteristics TO-220 FullPAK

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------------------------------------|------------|--------|------|------|--------------------|-------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.9 | $^\circ\text{C/W}$ | - |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 80 | $^\circ\text{C/W}$ | leaded |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | $^\circ\text{C}$ | 1.6mm (0.063 in.) from case for 10s |

¹⁾ Limited by $T_{j,max} < 150^\circ\text{C}$, Maximum Duty Cycle $D = 0.5$, TO220 equivalent

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ $V_{DClink}=400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

3 Electrical characteristics

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------|------|----------|---------------------------------------------------------------------------------------|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 500 | - | - | V | $V_{GS}=0V, I_D=1mA$ |
| Gate threshold voltage | $V_{(GS)th}$ | 2.50 | 3 | 3.50 | V | $V_{DS}=V_{GS}, I_D=0.51mA$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 1 | μA | $V_{DS}=500V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=500V, V_{GS}=0V, T_j=150^\circ C$ |
| Gate-source leakage current | I_{GSS} | - | - | 100 | nA | $V_{GS}=20V, V_{DS}=0V$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.17 | 0.19 | Ω | $V_{GS}=13V, I_D=6.2A, T_j=25^\circ C$ $V_{GS}=13V, I_D=6.2A, T_j=150^\circ C$ |
| Gate resistance | R_G | - | 3 | - | Ω | $f=1\text{ MHz, open drain}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------------------------------------|--------------|--------|------|------|------|----------------------------------------------------|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 1137 | - | pF | $V_{GS}=0V, V_{DS}=100V, f=1MHz$ |
| Output capacitance | C_{oss} | - | 68 | - | pF | $V_{GS}=0V, V_{DS}=100V, f=1MHz$ |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 56 | - | pF | $V_{GS}=0V, V_{DS}=0...400V$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 251 | - | pF | $I_D=constant, V_{GS}=0V, V_{DS}=0...400V$ |
| Turn-on delay time | $t_{d(on)}$ | - | 9.5 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=7.7A, R_G=3.4\Omega$ |
| Rise time | t_r | - | 8.5 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=7.7A, R_G=3.4\Omega$ |
| Turn-off delay time | $t_{d(off)}$ | - | 54 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=7.7A, R_G=3.4\Omega$ |
| Fall time | t_f | - | 7.5 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=7.7A, R_G=3.4\Omega$ |

Table 6 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|-------------------------------------------------|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 6.1 | - | nC | $V_{DD}=400V, I_D=7.7A, V_{GS}=0\text{ to }10V$ |
| Gate to drain charge | Q_{gd} | - | 24.5 | - | nC | $V_{DD}=400V, I_D=7.7A, V_{GS}=0\text{ to }10V$ |
| Gate charge total | Q_g | - | 47.2 | - | nC | $V_{DD}=400V, I_D=7.7A, V_{GS}=0\text{ to }10V$ |
| Gate plateau voltage | $V_{plateau}$ | - | 5.4 | - | V | $V_{DD}=400V, I_D=7.7A, V_{GS}=0\text{ to }10V$ |

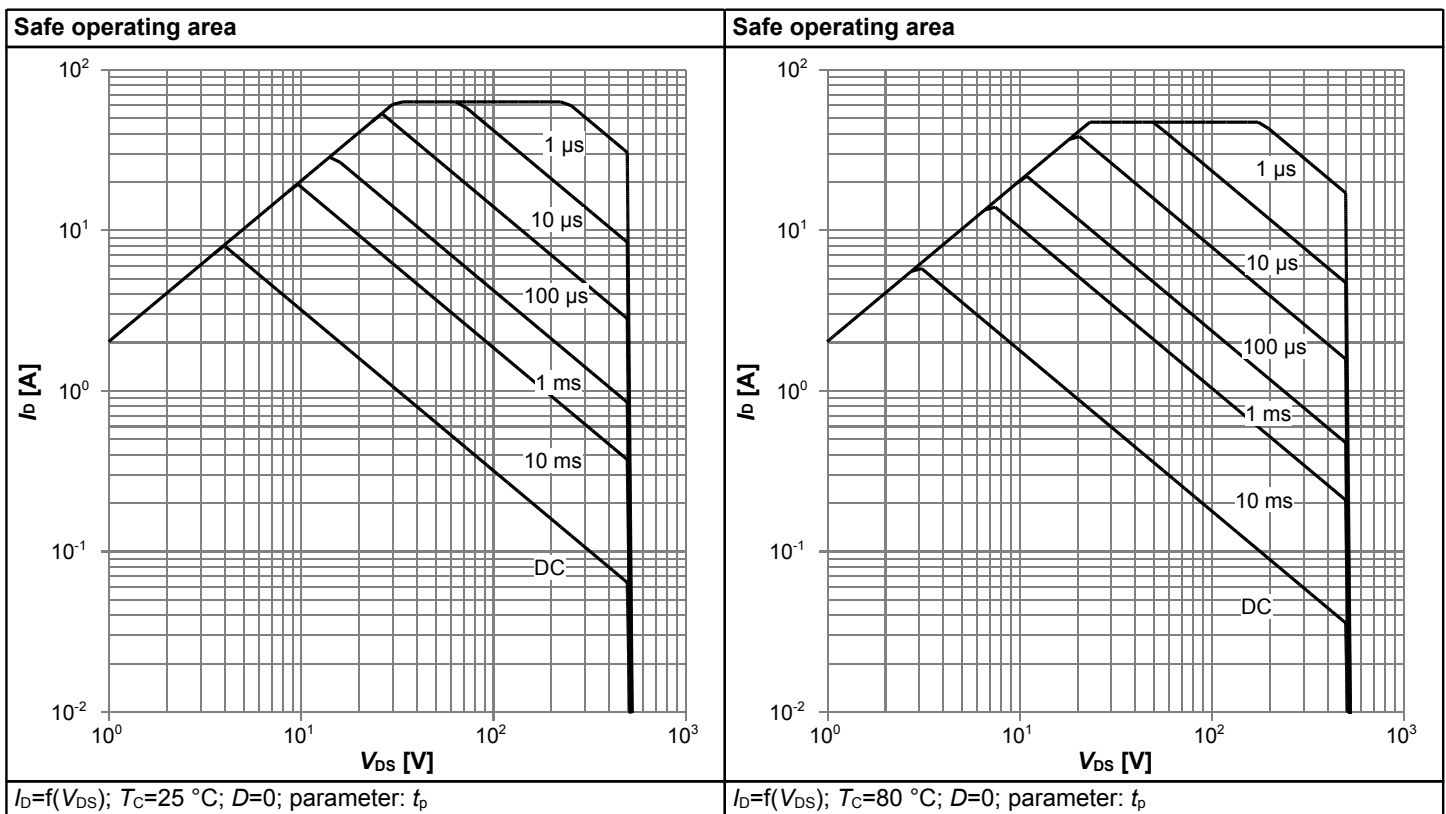
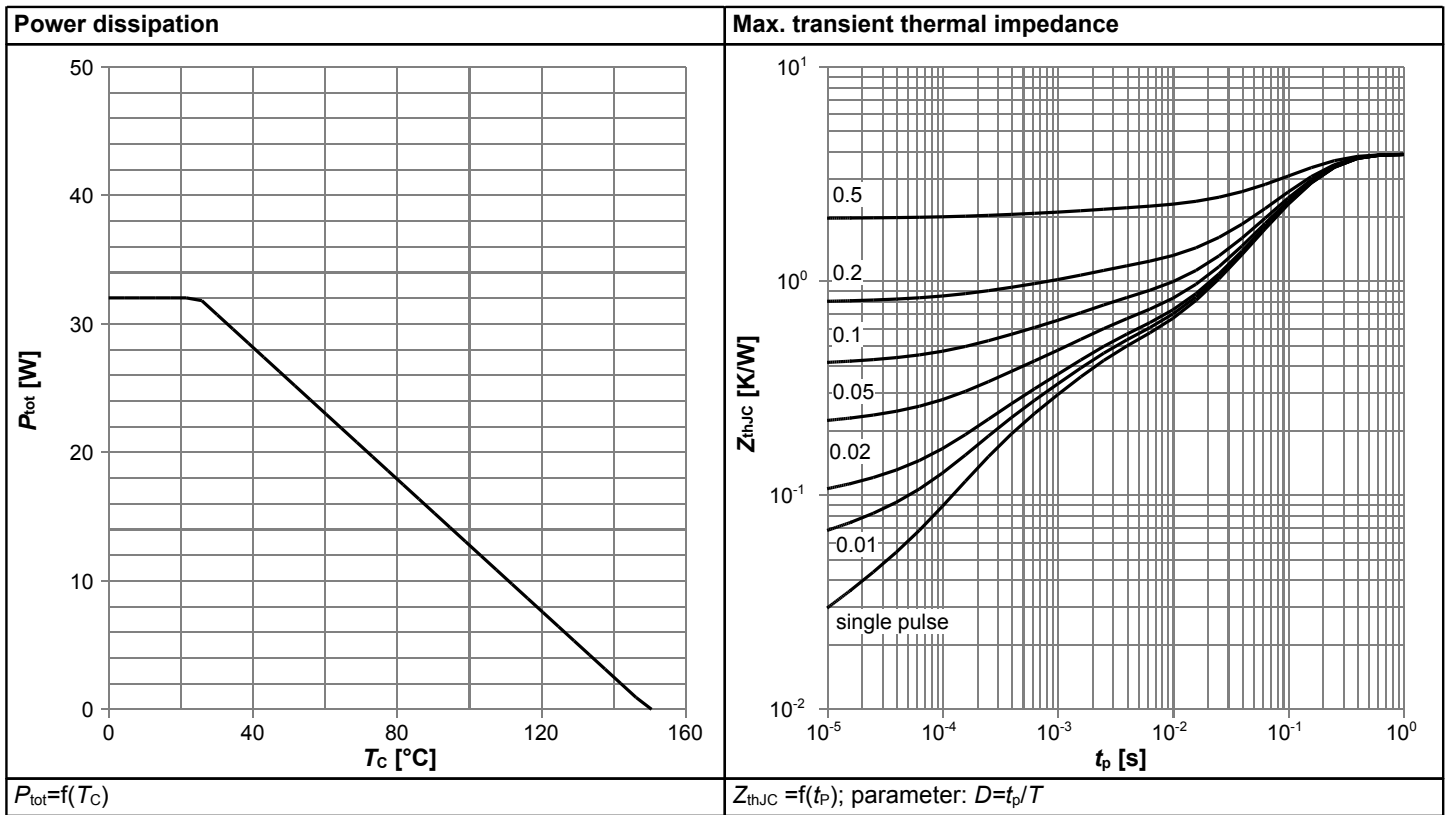
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

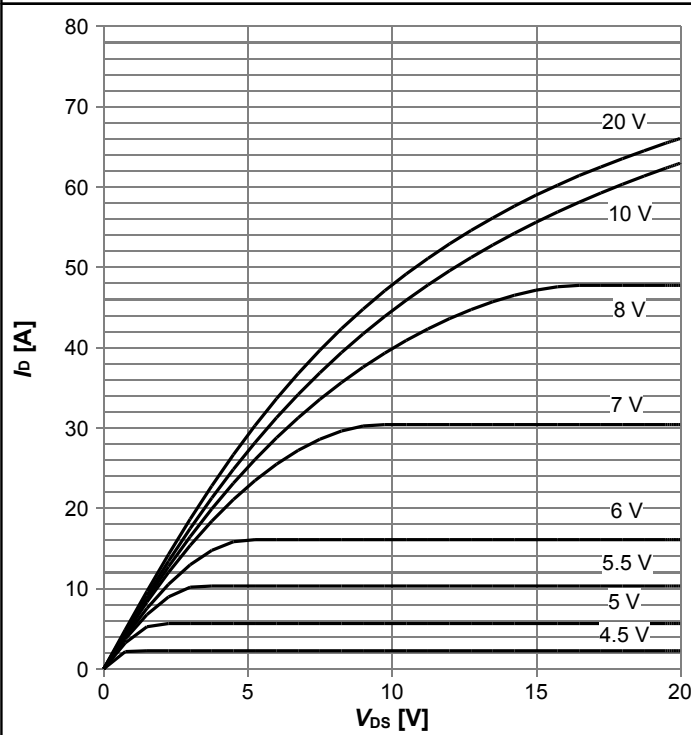
Table 7 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------|------------------------------------------|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.85 | - | V | $V_{GS}=0V, I_F=7.7A, T_i=25^\circ C$ |
| Reverse recovery time | t_{rr} | - | 280 | - | ns | $V_R=400V, I_F=7.7A, di_F/dt=100A/\mu s$ |
| Reverse recovery charge | Q_{rr} | - | 3.2 | - | μC | $V_R=400V, I_F=7.7A, di_F/dt=100A/\mu s$ |
| Peak reverse recovery current | I_{rrm} | - | 21.5 | - | A | $V_R=400V, I_F=7.7A, di_F/dt=100A/\mu s$ |

4 Electrical characteristics diagrams

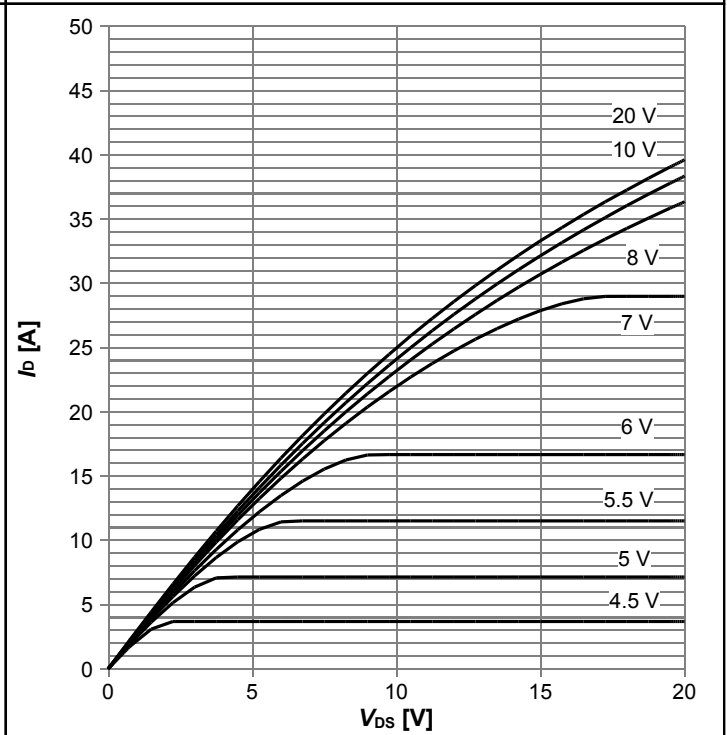


Typ. output characteristics $T_j=25^\circ\text{C}$



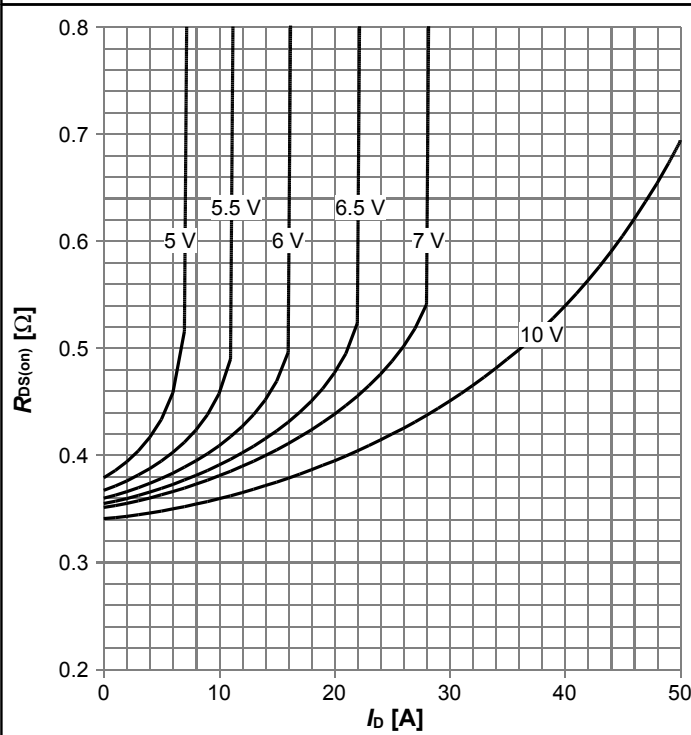
$I_D=f(V_{DS})$; $T_j=25^\circ\text{C}$; parameter: V_{GS}

Typ. output characteristics $T_j=125^\circ\text{C}$



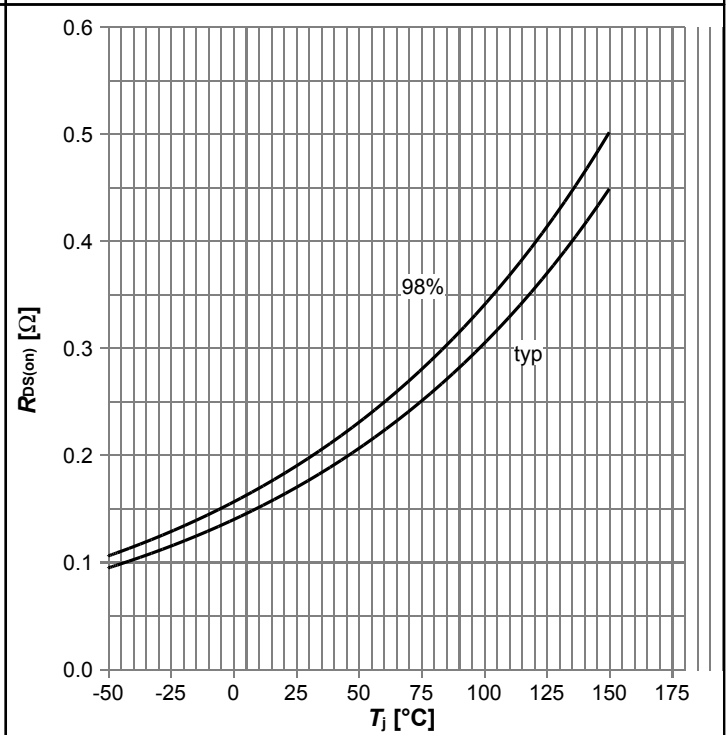
$I_D=f(V_{DS})$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D)$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

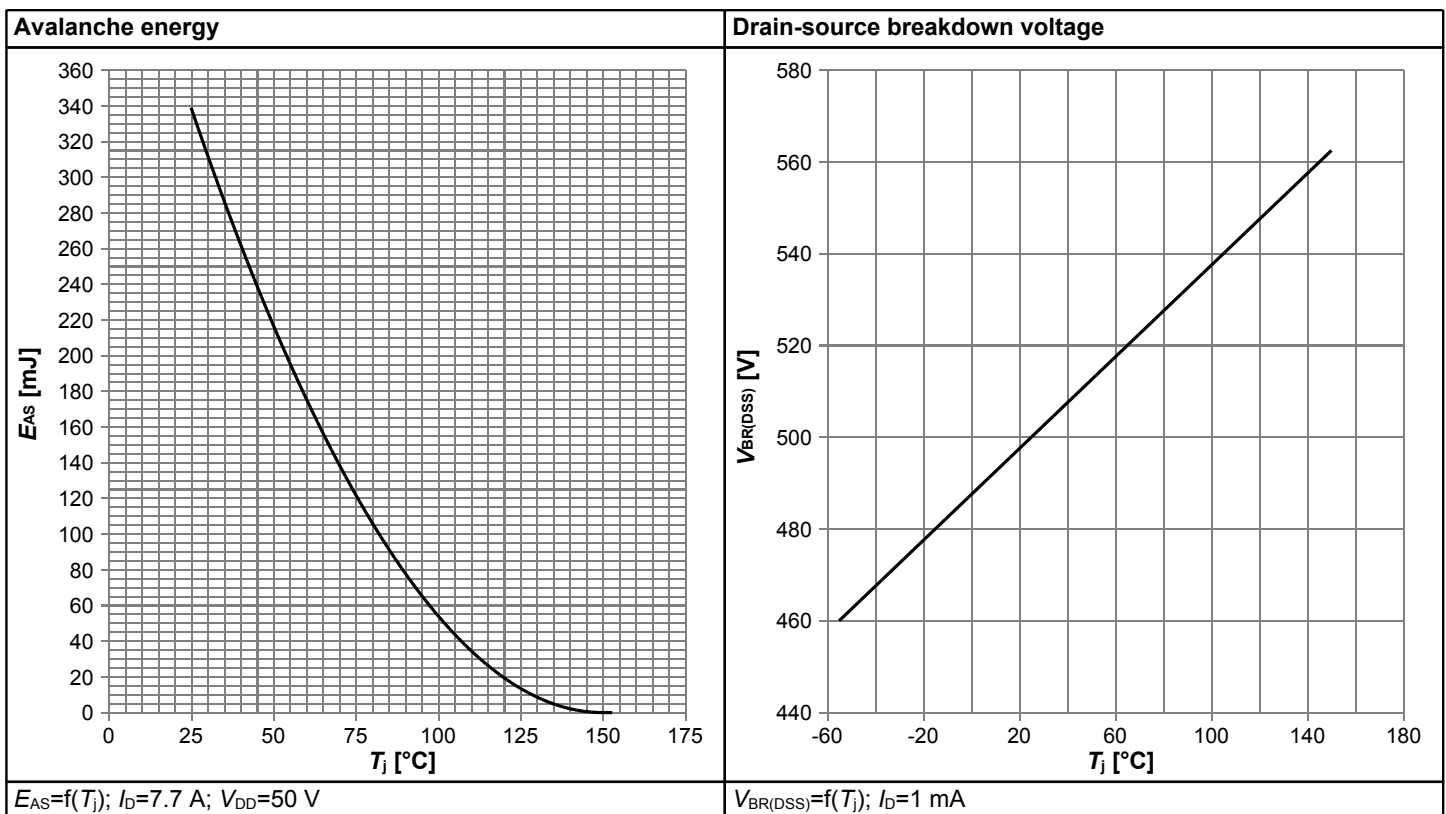
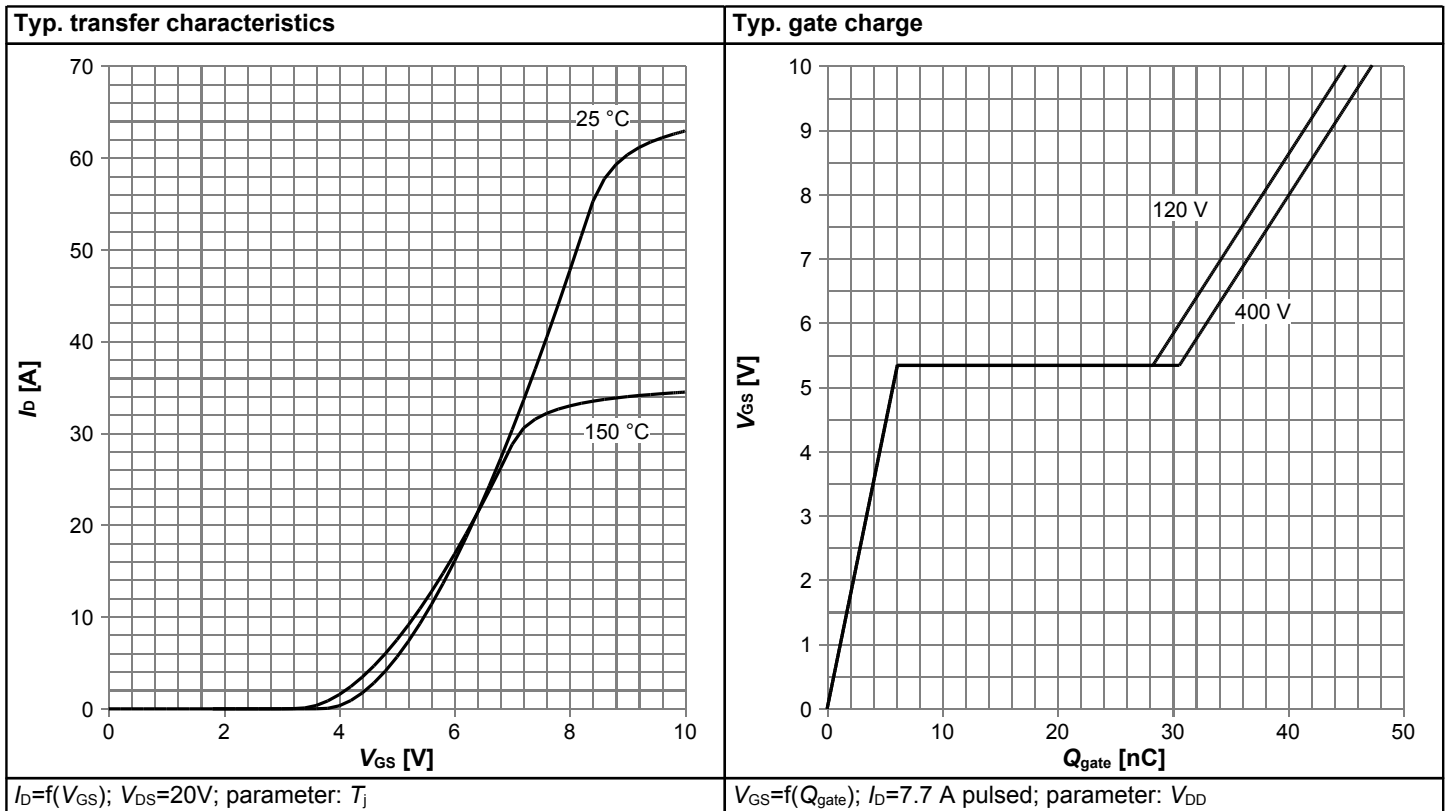
Drain-source on-state resistance

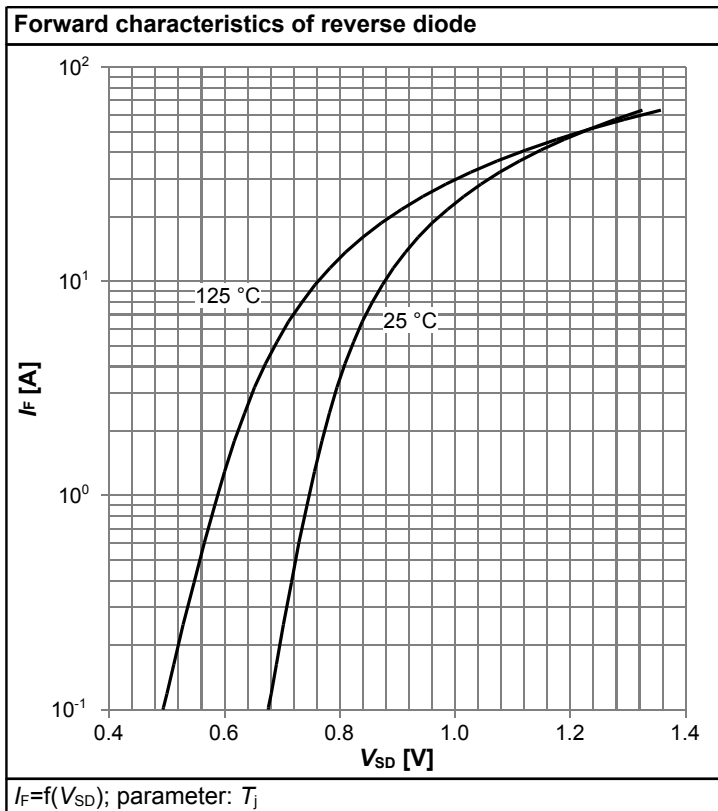
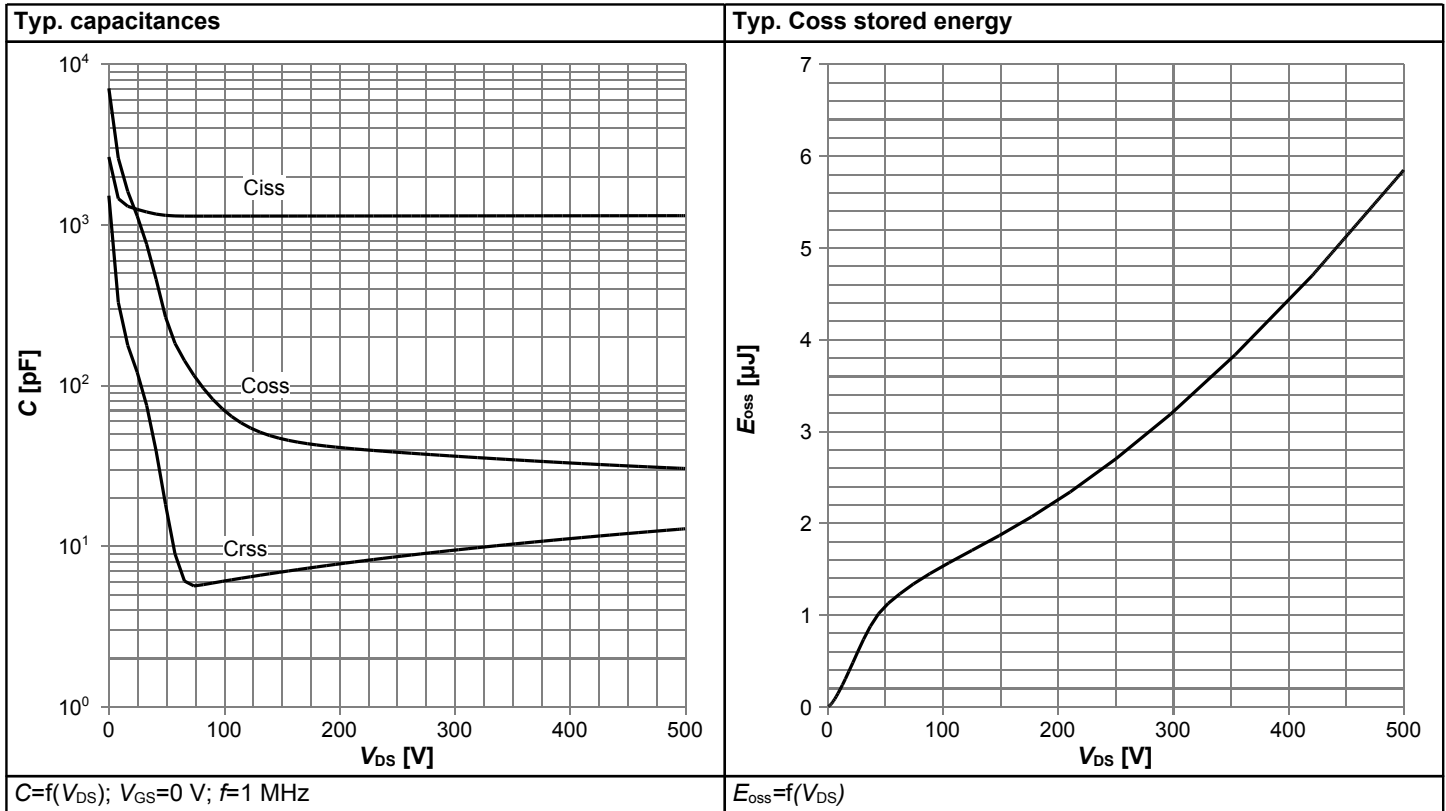


$R_{DS(on)}=f(T_j)$; $I_D=6.2\text{ A}$; $V_{GS}=13\text{ V}$

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IPA50R190CE





5 Test Circuits

Table 8 Diode characteristics

| Test circuit for diode characteristics | Diode recovery waveform |
|----------------------------------------|-------------------------|
| | |

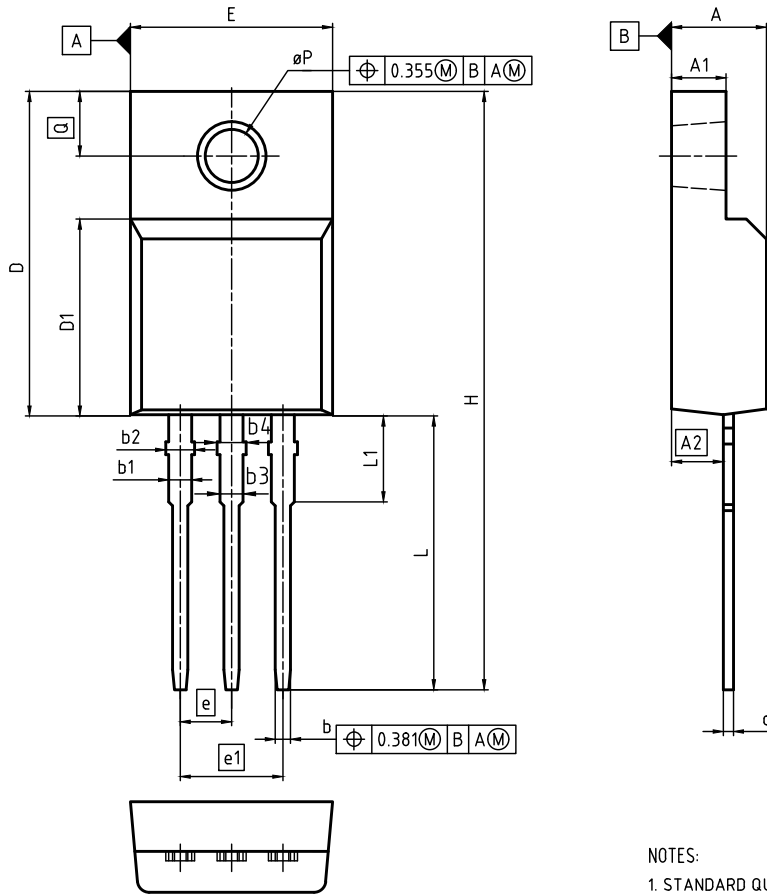
Table 9 Switching times

| Switching times test circuit for inductive load | Switching times waveform |
|-------------------------------------------------|--------------------------|
| | |

Table 10 Unclamped inductive load

| Unclamped inductive load test circuit | Unclamped inductive waveform |
|---------------------------------------|------------------------------|
| | |

6 Package Outlines



NOTES:

1. STANDARD QUALITY GRADE
2. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-281 NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS

DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.50 | 4.90 | 0.177 | 0.193 |
| A1 | 2.34 | 2.80 | 0.092 | 0.110 |
| A2 | 2.42 | 2.86 | 0.095 | 0.113 |
| b | 0.65 | 0.90 | 0.026 | 0.035 |
| b1 | 0.95 | 1.38 | 0.037 | 0.054 |
| b2 | 1.20 | 1.50 | 0.047 | 0.059 |
| b3 | 0.65 | 1.38 | 0.026 | 0.054 |
| b4 | 1.20 | 1.50 | 0.047 | 0.059 |
| c | 0.40 | 0.63 | 0.016 | 0.025 |
| D | 15.67 | 16.15 | 0.617 | 0.636 |
| D1 | 8.97 | 9.83 | 0.353 | 0.387 |
| E | 10.00 | 10.65 | 0.394 | 0.419 |
| e | 2.54 (BSC) | | 0.100 (BSC) | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H | 28.70 | 29.75 | 1.130 | 1.171 |
| L | 12.78 | 13.75 | 0.503 | 0.541 |
| L1 | 2.83 | 3.45 | 0.111 | 0.136 |
| øP | 3.00 | 3.38 | 0.118 | 0.133 |
| Q | 3.15 | 3.50 | 0.124 | 0.138 |

| |
|------------------------------------|
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| SCALE |
| EUROPEAN PROJECTION |
| ISSUE DATE 29-04-2016 |
| REVISION 01 |

Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS Webpage:** www.infineon.com
- **IFX Design tools:** www.infineon.com

500V CoolMOS™ CE Power Transistor

IPA50R190CE

Revision History

IPA50R190CE

Revision: 2016-07-12, Rev. 2.4

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|------------------------------------------------------------|
| 1.0 | 2011-06-07 | Release of final Data sheet |
| 2.0 | 2011-06-08 | Release of final data sheet |
| 2.1 | 2011-06-16 | Release of final data sheet |
| 2.2 | 2015-08-21 | change to standard grade qualification |
| 2.3 | 2016-06-10 | Updated ID ratings, package marking code & package drawing |
| 2.4 | 2016-07-12 | Changed marking information in page 1 |

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